IAP5 Rec'd PCT/PTO 01 FEB 2006 10/567729 OGOSH46USA

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re t	he Application of:)
) Examiner:
	Kazutoshi Kojima et al.)
) Group Art Unit:
Appli	cation No.:)
Corre	sponding International Filing No.:)
Corre	PCT/JP2004/011894)
		,)
Filed:	Herewith)
)
For:	SILICON CARBIDE EPITAXIAL	.)
	WAFER, METHOD FOR)
	PRODUCING SUCH WAFER,)
	AND SEMICONDUCTOR)
	DEVICE FORMED ON SUCH)
	WAFER)

Mail Stop PCT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

FIRST PRELIMINARY AMENDMENT

Sir:

Before calculating the filing fee, please amend the above-identified patent application as follows.

Amendments to the Claims are reflected in the listing of claims which begins on page two of this paper.

Remarks begin on page three of this paper.